

SANYO	No.4759	2SC4855
		NPN Epitaxial Planar Silicon Transistor Low-Voltage, Low-Current&High-Frequency Amp Applications

Features

- Low-voltage, low-current operation : $f_T = 5\text{GHz}$ typ.
($V_{CE} = 1\text{V}$, $I_C = 1\text{mA}$) : $|S_{21e}|^2 = 7.5\text{dB}$ typ ($f = 1\text{GHz}$).
: $NF = 2.6\text{dB}$ typ ($f = 1\text{GHz}$).

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Collector-to-Base Voltage	V_{CBO}	12	V
Collector-to-Emitter Voltage	V_{CEO}	6	V
Emitter-to-Base Voltage	V_{EBO}	1.5	V
Collector Current	I_C	15	mA
Collector Dissipation	P_C	80	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Collector Cutoff Current	I_{CBO}	$V_{CB} = 5\text{V}, I_E = 0$			1.0	μA
Emitter Cutoff Current	I_{EBO}	$V_{EB} = 1\text{V}, I_C = 0$			10	μA
DC Current Gain	h_{FE}	$V_{CE} = 1\text{V}, I_C = 1\text{mA}$	60*		270*	
Gain-Bandwidth Product	f_T	$V_{CE} = 1\text{V}, I_C = 1\text{mA}$		5		GHz
Output Capacitance	C_{ob}	$V_{CB} = 1\text{V}, f = 1\text{MHz}$		0.6	1.0	pF
Forward Transfer Gain	$ S_{21e} ^2$ (1)	$V_{CE} = 1\text{V}, I_C = 1\text{mA}, f = 1\text{GHz}$	5	7.5		dB
	$ S_{21e} ^2$ (2)	$V_{CE} = 2\text{V}, I_C = 3\text{mA}, f = 1\text{GHz}$		11.5		dB
Noise Figure	NF(1)	$V_{CE} = 1\text{V}, I_C = 1\text{mA}, f = 1\text{GHz}$		2.6	4.5	dB
	NF(2)	$V_{CE} = 2\text{V}, I_C = 3\text{mA}, f = 1\text{GHz}$		1.9		dB

* : The 2SC4855 are classified by 1mA h_{FE} as follows:

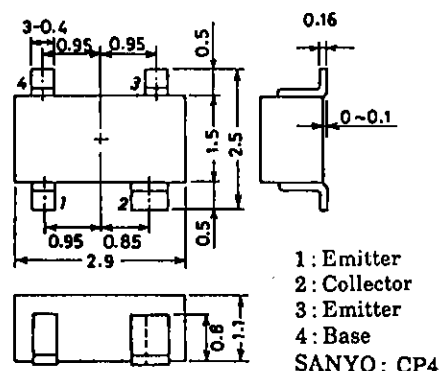
60	3	120	90	4	180	135	5	270
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Marking : CN

h_{FE} rank : 3,4,5

Package Dimensions 2110A

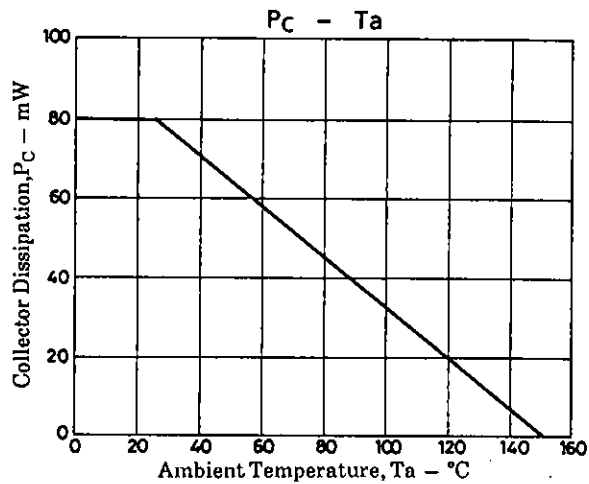
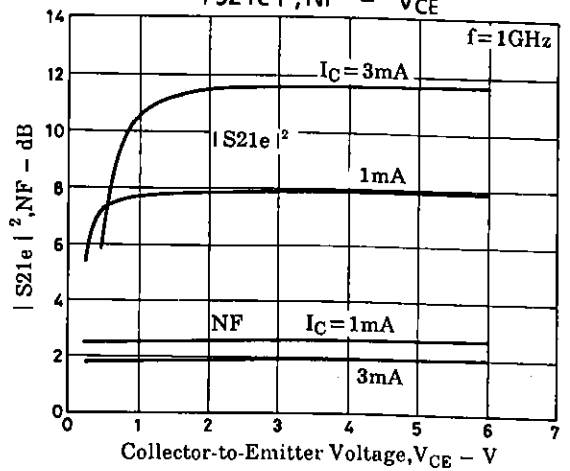
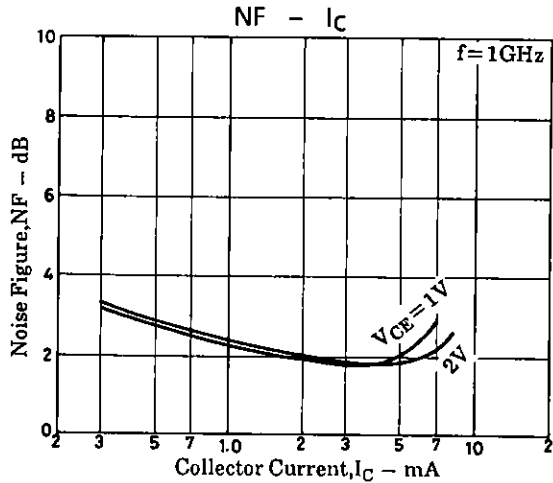
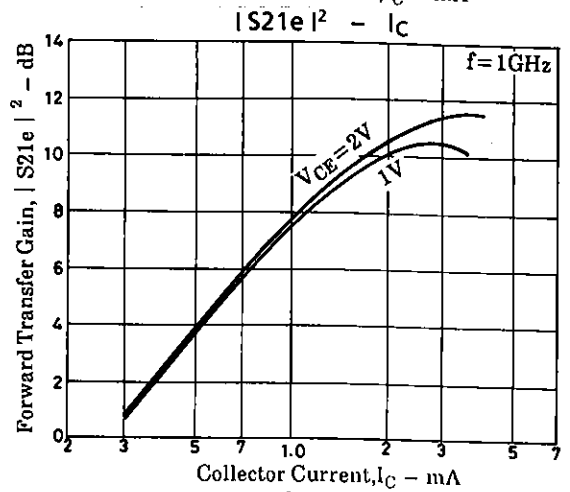
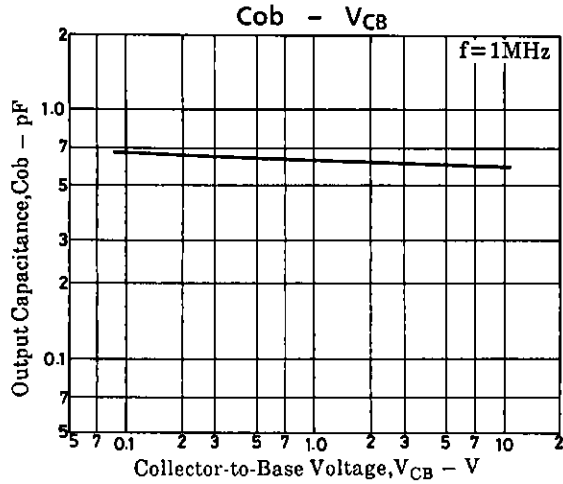
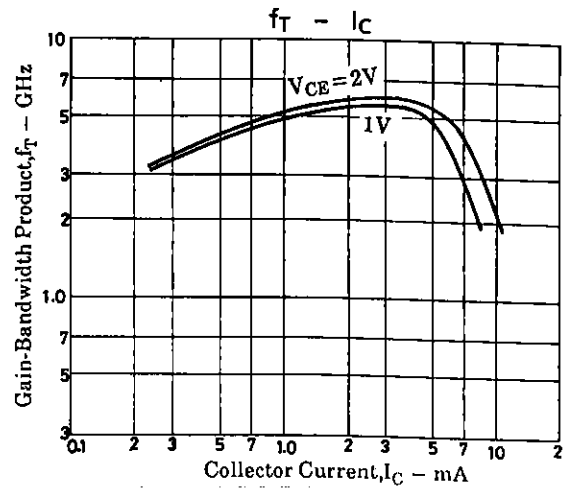
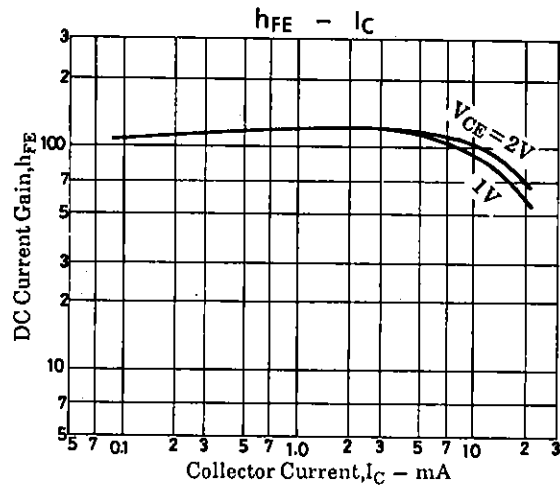
(unit : mm)



SANYO Electric Co., Ltd. Semiconductor Business Headquarters

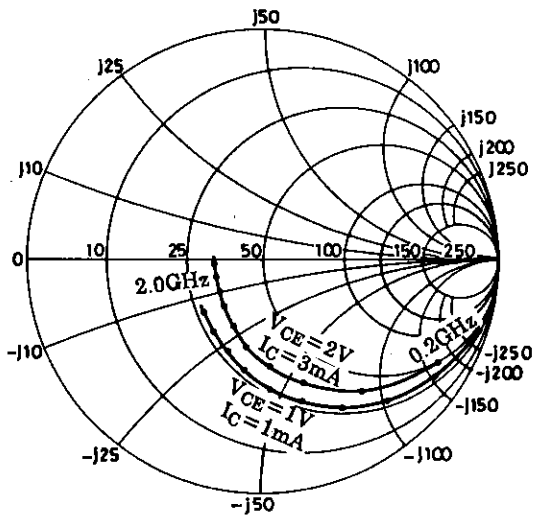
TOKYO OFFICE Tokyo Bldg., 1-10, 1 Chome, Ueno, Taito-ku, TOKYO, 110 JAPAN

90794MT (KOTO) BX-0759 No.4759-1/4

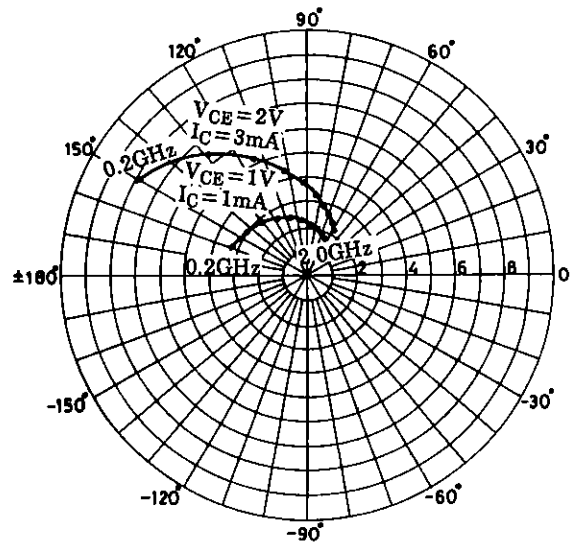


S Parameters

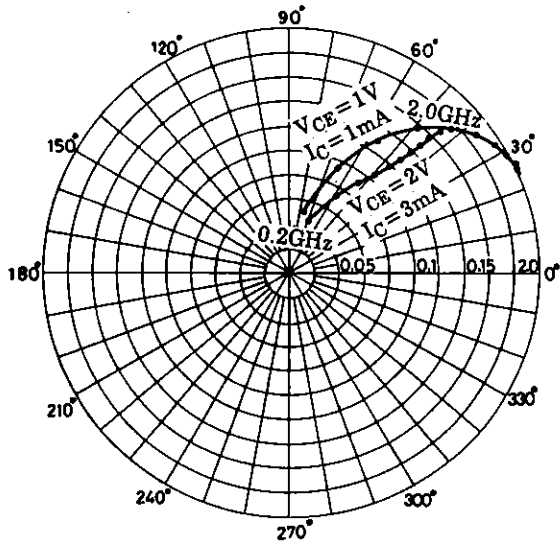
S11e
f = 200 ~ 2000 MHz (200 MHz step)



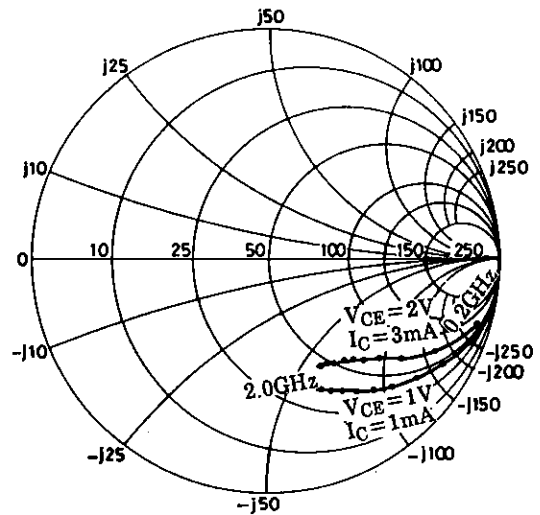
S21e
f = 200 ~ 2000 MHz (200 MHz step)



S12e
f = 200 ~ 2000 MHz (200 MHz step)



S22e
f = 200 ~ 2000 MHz (200 MHz step)



S Parameters (Common emitter)

 $V_{CE}=1V$, $I_C=1mA$, $Z_0=50\Omega$

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
200	0.944	-18.0	3.276	159.9	0.050	76.8	0.981	-12.0
400	0.869	-34.2	3.037	143.8	0.093	65.5	0.928	-22.2
600	0.786	-48.9	2.778	130.2	0.128	56.5	0.865	-31.1
800	0.706	-62.0	2.550	117.6	0.155	48.8	0.808	-38.6
1000	0.619	-75.4	2.379	106.1	0.173	42.3	0.753	-45.7
1200	0.547	-87.4	2.165	95.7	0.186	36.9	0.712	-51.2
1400	0.473	-100.1	2.022	85.9	0.194	32.4	0.675	-56.1
1600	0.417	-111.7	1.840	77.4	0.198	28.9	0.639	-60.4
1800	0.371	-125.2	1.745	69.9	0.202	26.4	0.614	-64.1
2000	0.343	-139.3	1.639	62.2	0.201	25.2	0.595	-67.6

 $V_{CE}=2V$, $I_C=3mA$, $Z_0=50\Omega$

Freq (MHz)	$ S_{11} $	$\angle S_{11}$	$ S_{21} $	$\angle S_{21}$	$ S_{12} $	$\angle S_{12}$	$ S_{22} $	$\angle S_{22}$
200	0.844	-30.5	7.785	149.6	0.043	71.0	0.933	-17.4
400	0.688	-53.7	6.308	129.2	0.072	59.3	0.808	-28.8
600	0.545	-72.1	5.182	113.8	0.091	52.6	0.705	-36.3
800	0.451	-86.7	4.315	102.3	0.104	49.2	0.632	-41.6
1000	0.374	-102.0	3.713	92.2	0.117	47.0	0.590	-46.0
1200	0.308	-115.4	3.225	83.5	0.127	45.9	0.564	-49.5
1400	0.260	-130.6	2.823	75.5	0.137	45.0	0.541	-53.1
1600	0.230	-145.2	2.515	68.8	0.146	44.5	0.525	-56.8
1800	0.215	-160.5	2.296	63.0	0.155	44.2	0.510	-60.3
2000	0.213	-177.0	2.143	56.9	0.166	43.8	0.506	-63.4

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